

CMUSH05-4

**SURFACE MOUNT
HIGH CURRENT, LOW V_F
SILICON SCHOTTKY DIODE**

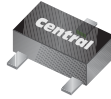


www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMUSH05-4 is a HIGH CURRENT, LOW V_F 40 volt Schottky Diode packaged in a space saving SOT-523 surface mount case. This ULTRAmi™ device has been designed for small signal general purpose applications when small size and operational efficiency are prime requirements.

ULTRAmi™



LOW
 V_F

SOT-523 CASE

MARKING CODE: U54

SPECIFICATIONS:

- Low V_F = 0.35V max @ 100mA
- V_{RRM} = 40V
- I_F = 500mA

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current, $t_p \leq 1.0\text{ms}$
Peak Forward Surge Current, $t_p = 8.0\text{ms}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{RRM} 40
 I_F 500
 I_{FRM} 3.5
 I_{FSM} 10
 P_D 250
 T_J, T_{stg} -65 to +150
 θ_{JA} 500

UNITS

V
mA
A
A
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=10\text{V}$		20	μA
I_R	$V_R=30\text{V}$		100	μA
BV_R	$I_R=500\mu\text{A}$	40		V
V_F	$I_F=100\mu\text{A}$		0.13	V
V_F	$I_F=1.0\text{mA}$		0.21	V
V_F	$I_F=10\text{mA}$		0.27	V
V_F	$I_F=100\text{mA}$		0.35	V
V_F	$I_F=500\text{mA}$		0.47	V
C_T	$V_R=1.0\text{V}, f=1.0\text{MHz}$		50	pF

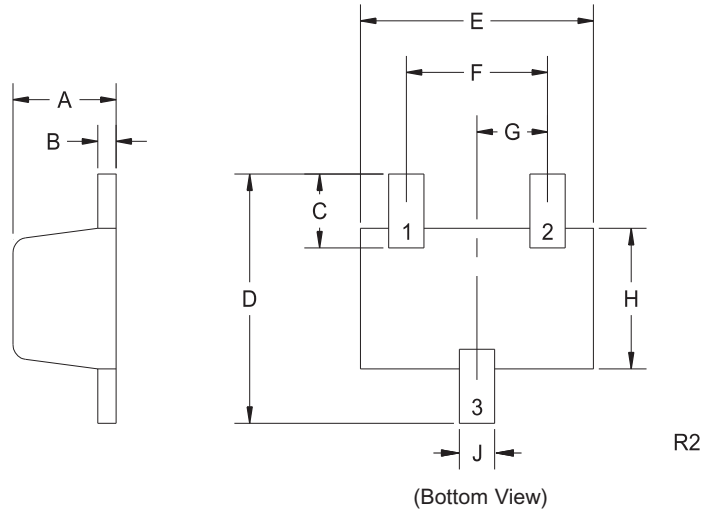
R1 (9-February 2010)

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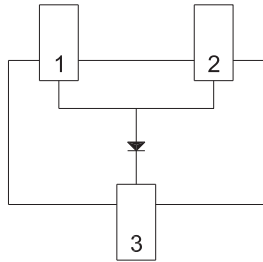
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SOT-523 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.023	0.031	0.58	0.78
B	0.002	0.008	0.04	0.20
C	0.013	0.021	0.34	0.54
D	0.059	0.067	1.50	1.70
E	0.059	0.067	1.50	1.70
F	0.035	0.043	0.90	1.10
G	0.020		0.50	
H	0.031	0.039	0.78	0.98
J	0.010	0.014	0.25	0.35

SOT-523 (REV: R2)

LEAD CODE:

- 1) Anode
- 2) Anode
- 3) Cathode

MARKING CODE: U54

R1 (9-February 2010)